

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

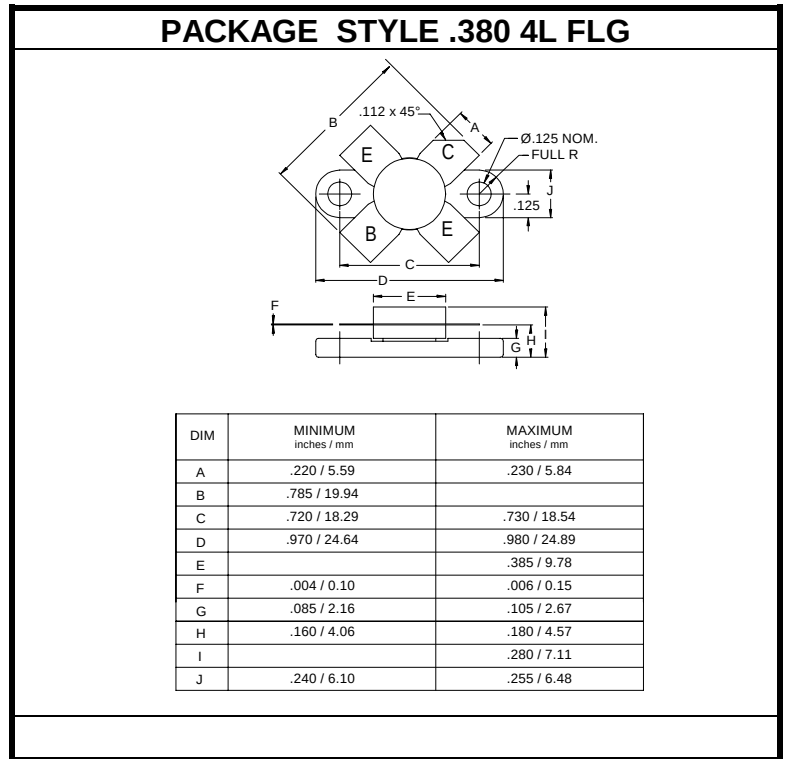
The **ASI BLW76** is Designed for use in class-AB or class-B operated high power transmitters in the H.F. and V.H.F bands and, as a Linear amplifier in the H.F. band.

FEATURES:

- $P_G = 18$ dB min. at 75 W/30 MHz
- $IMD_3 = -30$ dBc max. at 75 W (PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	1.05 $^\circ C/W$



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CEO}	I _C = 50 mA			35			V
BV _{CER}	I _C = 50 mA	R _{BE} = 10 Ω		60			V
BV _{EBO}	I _E = 10 mA			4.0			V
I _{CES}	V _E = 28 V					5.0	mA
h _{FE}	V _{CE} = 5.0 V	I _C = 1.0 A		10		100	---
C _{ob}	V _{CB} = 28 V f = 1.0 MHz					80	pF
G _{PE}	V _{CE} = 25 V	I _{CQ} = 3.2 A	f = 225 MHz	13.5	14.5	-55	dB
IMD ₃	P _{REF} = 16 W	Vision = -8 dB Side Band = -16 dB	Snd. = -7 dB				dBc